

Abstracts

Ka-Band 2 Watt Power GaAs MMIC (1989 Vol. III [MWSYM])

S. Arai, T. Yoshida, K. Kai, S. Takatsuka, Y. Oda and S. Yanagawa. "Ka-Band 2 Watt Power GaAs MMIC (1989 Vol. III [MWSYM])." 1989 MTT-S International Microwave Symposium Digest 89.3 (1989 Vol. III [MWSYM]): 1105-1108.

High-power Ka-band power GaAs MMICs have been developed using distributed-element impedance transforming technique. At 30 GHz, an output power of 2 W with 3.3 dB gain and a saturation output power of 3 W have been obtained from 9.6 mm gate width power GaAs FET MMIC. These output powers are the highest values reported to date on Ka-band FETs.

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